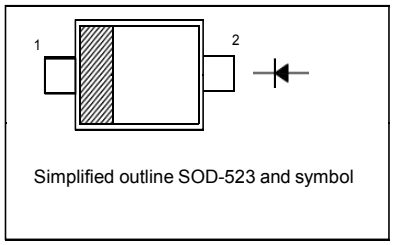
Surface Mount Schottky Barrier Diodes

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

Features

• Low Forward Voltage



Simplified outline SOD-523 and symbol

MARKING

SD103AWT:S4	SD103BWT:S5	SD103CWT:S6

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage	SD103AWT SD103BWT SD103CWT	V_{RRM}	40 30 20	V
Reverse Voltage	SD103AWT SD103BWT SD103CWT	V_R	40 30 20	V
Average Forward Rectified Current		$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at t = 1 s		I_{FSM}	2	A
Power Dissipation		P_{tot}	150	mW
Operating Junction Temperature Range		T_j	- 40 to + 125	°C
Storage Temperature Range		T_{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at I_R = 10 µA	SD103AWT SD103BWT SD103CWT	$V_{(BR)R}$	40 30 20	- - -	- - -	V
Reverse Leakage Current at V_R = 30 V at V_R = 20 V at V_R = 10 V	SD103AWT SD103BWT SD103CWT	I_R	- - -	- - -	5 5 5	µA
Forward Voltage at I_F = 20 mA at I_F = 200 mA		V_F	- -	- -	0.37 0.6	V
Total Capacitance at V_R = 0 V, f = 1 MHz		C_T	-	50	-	pF
Reverse Recovery Time at I_F = I_R = 200 mA, I_{rr} = 0.1 I_R, R_L = 100 Ω		t_{rr}	-	10	-	ns

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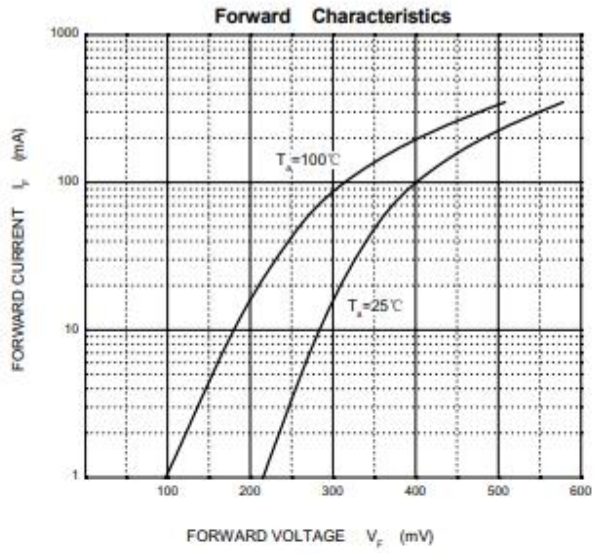
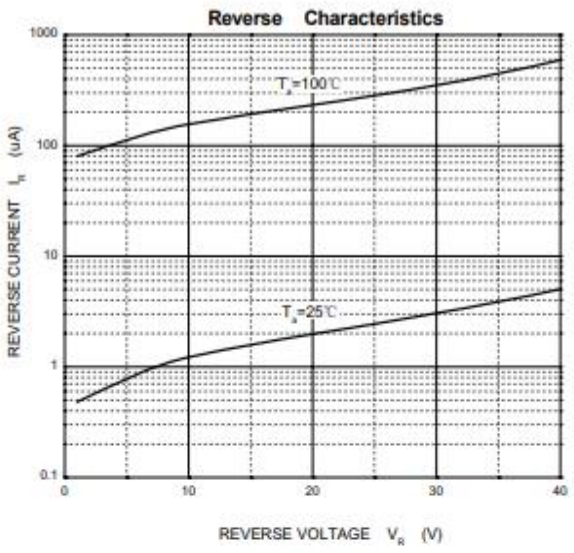
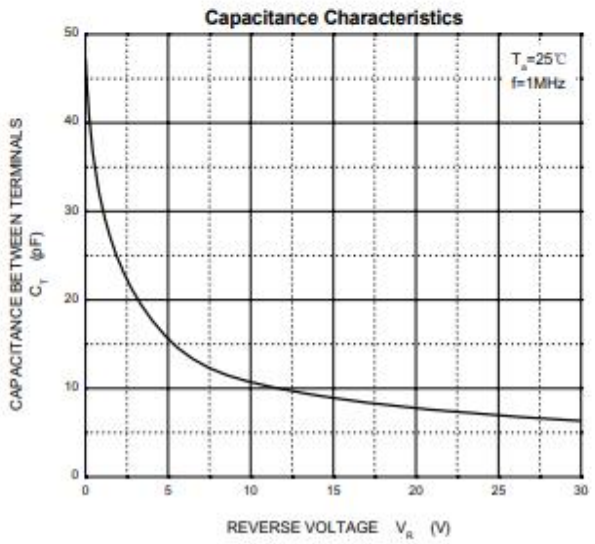
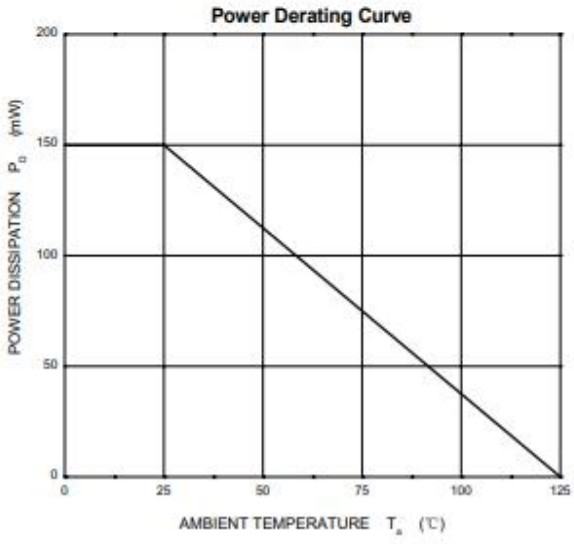
Typical Characteristics









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